ATR560N80S-Q1

N-Channel Super Junction Power MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
800V	560mΩ@10V	9A

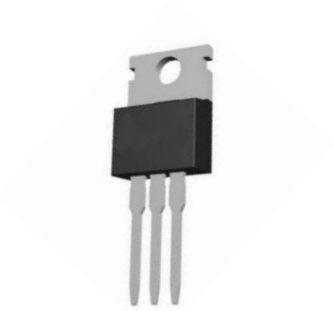
Feature

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Ultra Low Gate Charge cause lower driving requirements
- Suffix "-Q1" for AEC-Q101

Application

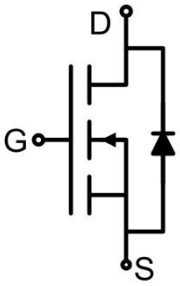
- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）

Package



TO-220AB

Circuit diagram



Marking

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Absolute maximum ratings (T_C=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	800	V
Gate-Source Voltage (V_{DS} =0V) AC (f>1Hz)	V_{GS}	±30	V
Continuous Drain Current	I_D	9	A
Continuous Drain Current(T_C=100℃)	I_D(100℃)	6	A
Pulsed Drain Current[1)]	I_{DM}	36	A
Maximum Power Dissipation	P_D	131	W
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	0.95	℃/W
Single pulse avalanche energy[2)]	E_{AS}	290	mJ
Avalanche current[1)]	I_{AR}	2.8	A
Repetitive Avalanche energy , t_{AR} limited by T_{jmax} [1)]	E_{AR}	1.4	mJ
Drain Source voltage slope, V_{DS}≤480V	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS}≤480V,I_{SD}<I_D	dv/dt	15	V/ns
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55 ~ +150	℃

Electrical characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	800			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =800V,V_{GS} =0V, Tc=25℃			1	μA
		V_{DS} =800V,V_{GS} = 0V, Tc=125℃			100	
Gate-body leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V			±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	3.0	3.5	4.0	V
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} =10V, I_D =4A		480	560	mΩ
Dynamic characteristics[3)]						
Input Capacitance	C_{iss}	V_{DS} =50V,V_{GS} =0V, f =1.0MHz		1200		pF
Output Capacitance	C_{oss}			75		
Reverse Transfer	C_{rss}			0.3		
Total Gate Charge	Q_g	V_{DS} =480V,V_{GS} =10V, I_D =9A		25		nC
Gate-Source Charge	Q_{gs}			8		
Gate-Drain Charge	Q_{gd}			8.5		
Turn-on delay time	$t_{d(on)}$	V_{DD}=480V, V_{GS} =10V, I_D =5A,R_G=2.3Ω		16		nS
Turn-on rise time	t_r			11		
Turn-off delay time	$t_{d(off)}$			58		
Turn-off fall time	t_f			10		
Source-Drain Diode characteristics						
Diode Forward Current	I_{SD}	T_C =25℃			9	A
Source-drain current	I_{SDM}				36	A
Diode Forward voltage	V_{SD}	V_{GS} =0V, I_{SD} =9A, T_j =25℃			1.2	V
Reverse Recovery Time	t_{rr}	I_F =5A,di/dt =100A/μs, T_j =25°C		240		nS
Reverse Recovery Charge	Q_{rr}			1.1		μC
Peak Reverse Recovery Current	I_{mm}			9		A

Notes:

1) Repetitive Rating: Pulse width limited by maximum junction temperature.

2) Tj=25°C,V_{DD}=50V,V_G=10V,R_G=25Ω

3) Guaranteed by design, not subject to production

Typical Characteristics

Figure1. Safe operating area

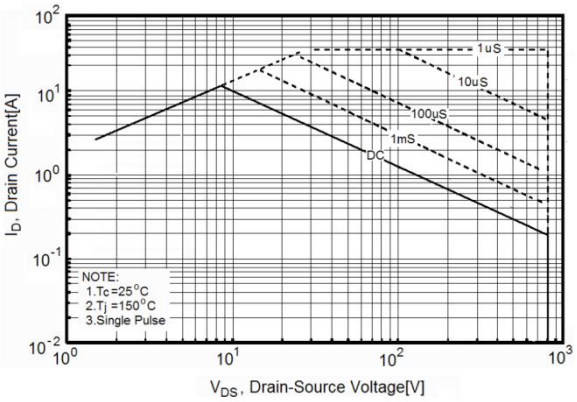


Figure2. Source-Drain Diode Forward Voltage

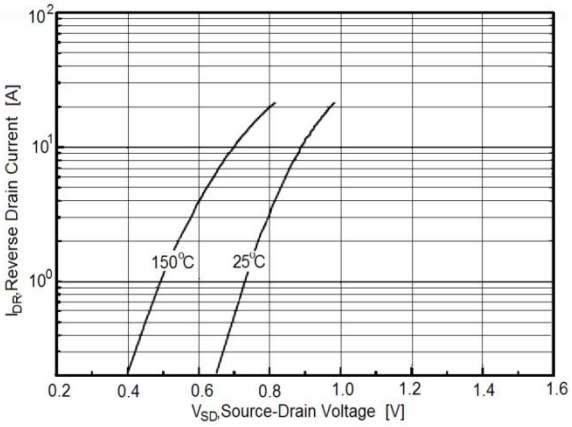


Figure3. Output characteristics

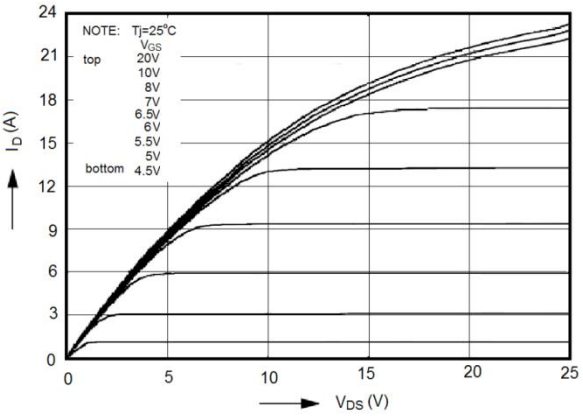


Figure4. Transfer characteristics

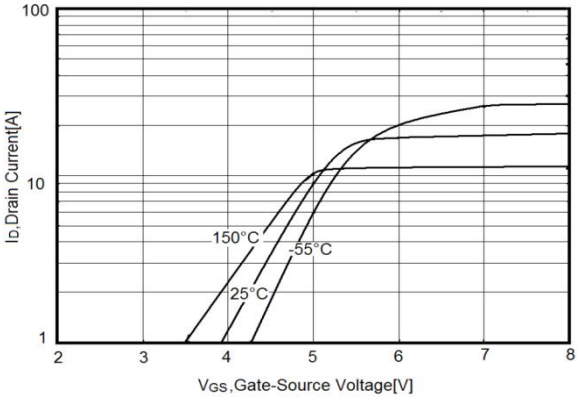


Figure5. Static drain-source on resistance

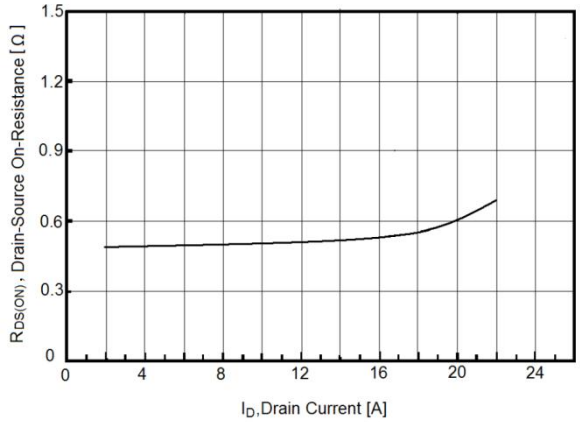
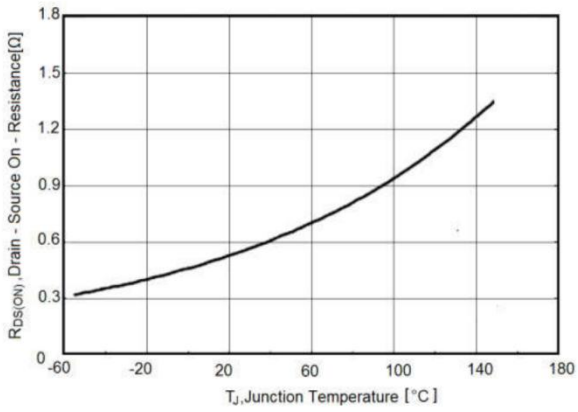


Figure6. $R_{DS(ON)}$ vs Junction Temperature



Typical Characteristics

Figure7. BV_{DSS} vs Junction Temperature

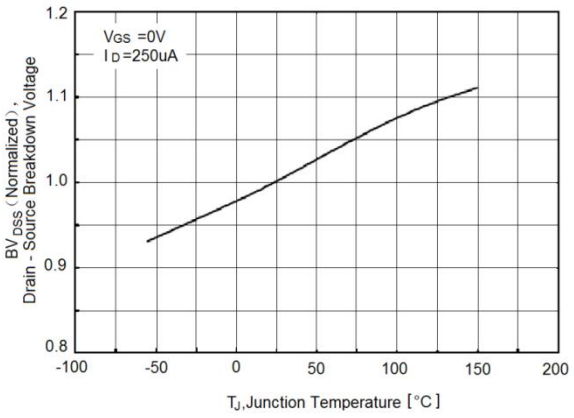


Figure8. Maximum I_D vs Junction Temperature

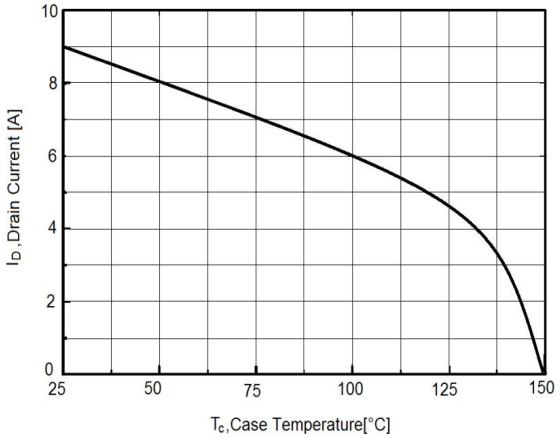


Figure9 . Gate charge waveforms

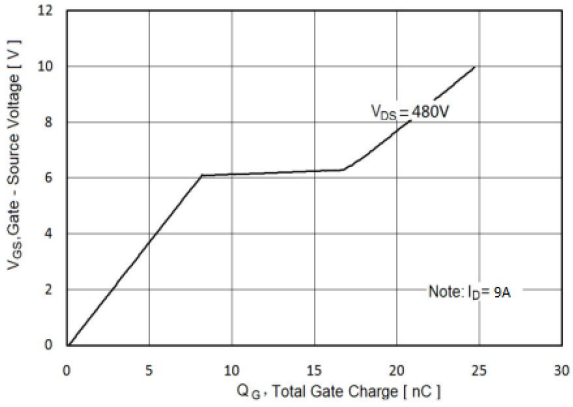


Figure10. Capacitance

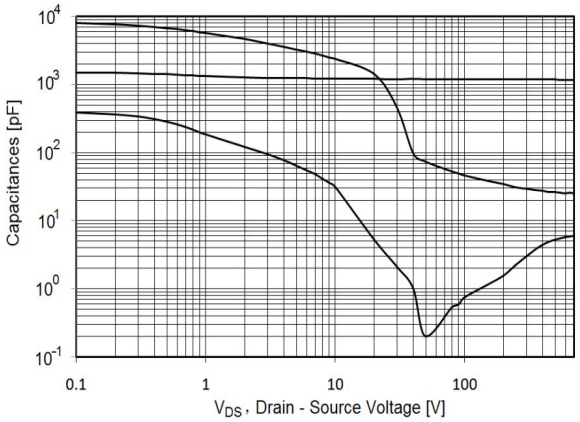
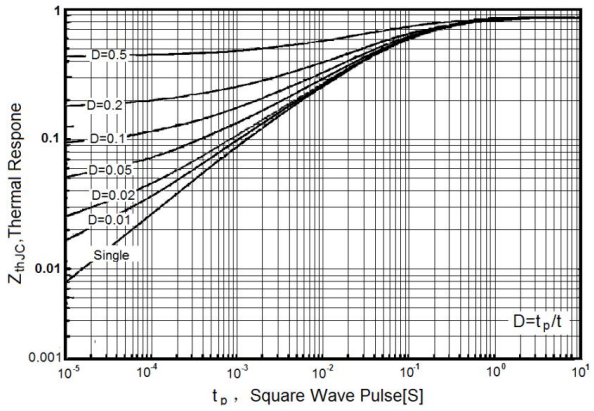
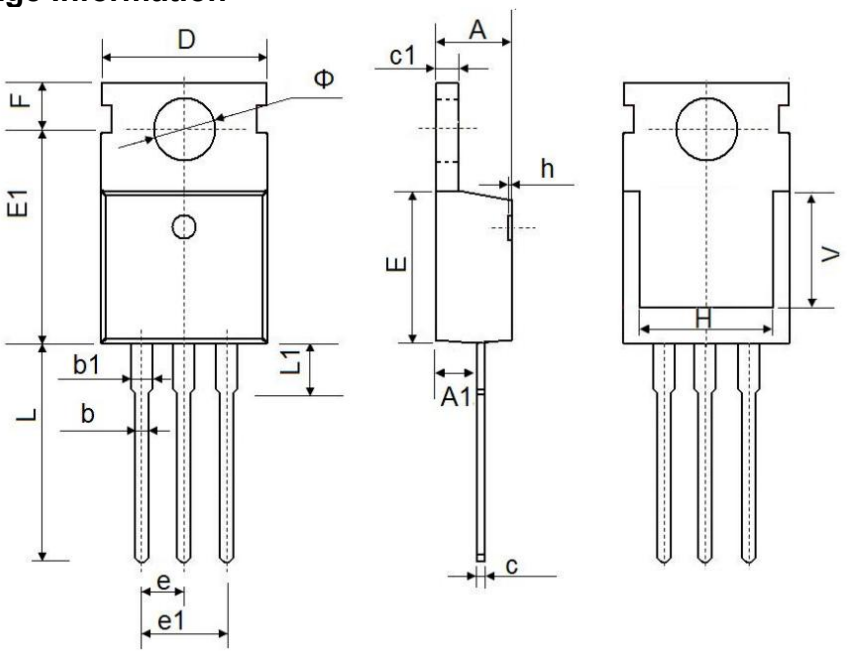


Figure11. Transient Thermal Impedance



TO-220AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.200	4.600	0.165	0.181
A1	2.250	2.550	0.089	0.100
b	0.700	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150